

# **Dual N-channel MOSFET**

# KFCAB22075NL Datasheet

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Mark Identifier

2.93

(Top View)

(Front View)

(Bottom View)

7 (S1)

DG FET

Unit: mm



#### 1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET for lithium-ion secondary battery protection circuits.

#### 2. FEATURES

- Source-source On-state Resistance: RSS(on) typ = 1.65 mΩ (VGS = 3.8 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

#### 3. MARKING SYMBOL: KL

#### 4. PACKAGING

Embossed type (Thermo-compression sealing): 8,000 pcs / reel (standard)

#### 5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

(MOSFET: CG FET, DG FET)

Parameter		Symbol	Rating	Unit	
Source-source Voltage	VSS	22	V		
Gate-source Voltage		VGS	± 12	V	
	DC *1	IS1	17.6		
Course Current	DC *2	IS2	31.6	٨	
Source Current	DC *3	IS3	42.9	А	
	Pulsed *4	ISp	176		
Dady Diada	DC *1	IF1	1.2		
Body Diode Forward Current	DC *2	IF2	3.5	Α	
Forward Current	DC *3	IF3	6.2		
	DC *1	PD1	0.59		
Total Power Dissipation	DC *2	PD2	1.90	W	
	DC *3	PD3	3.50		
Operating Junction and Storage Temperature Range		Tj, Tstg	- 55 to + 150	°C	

# 1, 2, 3, 4, 5, 6, 7. Source1 (DG FET) 8. Gate1 (DG FET) 9, 10, 11, 12, 13, 14, 15. Source2 (CG FET) 16. Gate2 (CG FET) TCSP2629010-N1 Package **Equivalent Circuit** 8 (DG) 16 (CG) Rg Rg DĞ) (CĞ 9, 10, 11, 1, 2, 3, 4, 5, 6, 12, 13, 14,

15 (S2)

**CG FET** 

#### 6. THERMAL CHARACTERISTICS Ta = 25 °C

Parameter	Symbol	Rating	Unit
	Rth1 *1, 2	211	
Thermal Resistance (ch-a)	Rth2*1,3	66	°C/W
	Rth3 *1, 4	35	

Note \*1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board partially covered with copper pad (41 mm $^2$  area, 36  $\mu$ m thickness).

- \*2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board fully covered with copper pad (612 mm² area, 36 μm thickness).
- \*3 Mounted on ceramic board (70 mm x 70 mm x t1.0 mm).
- \*4  $t = 10 \mu s$ , Duty Cycle  $\leq 1 \%$ .



## 7. ELECTRICAL CHARACTERISTICS Ta = 25 °C ± 3 °C

(MOSFET: CG FET, DG FET)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	22			V
Zero Gate Voltage Source Current	ISSS	VSS = 22 V, VGS = 0 V			1	μΑ
Gata source Leakage Current	IGSS1	VGS = ± 8 V, VSS = 0 V			± 0.5	
Gate-source Leakage Current	IGSS2	VGS = ± 5 V, VSS = 0 V			± 0.1	μA
Gate-source Threshold Voltage	Vth	IS = 1.43 mA, VSS = 10 V	0.35	0.90	1.40	V
	RSS(on)1	IS = 8.8 A, VGS = 4.5 V	1.30	1.60	1.85	mΩ
Source-source On-state Resistance	RSS(on)2	IS = 8.8 A, VGS = 3.8 V	1.35	1.65	1.90	
Source-source On-state Resistance	RSS(on)3	IS = 8.8 A, VGS = 3.1 V	1.40	1.80	2.55	
	RSS(on)4	IS = 8.8 A, VGS = 2.5 V	1.45	2.10	2.10 4.20	
Body Diode Forward Voltage	VF(s-s)	IF = 8.8 A, VGS = 0 V		0.70	0.82	V
Input Capacitance *1	Ciss		5800	8250	10750	
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		660		pF
Reverse Transfer Capacitance *1	Crss			610		
Total Gate Charge *1	Qg	VDD = 10 V		74		
Gate-source Charge *1	Qgs	VGS = 0 to 4 V		14		nC
Gate-drain Charge *1	Qgd	IS = 17.6 A		17		

(MOSFET: CG FET)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Turn-on Delay Time *1, *2	td(on)1	VDD = 10 V, VGS = 0 to 4 V		0.08		
Rise Time *1, *2	tr1	IS = 8.8 A		0.20		μs
Turn-off Delay Time *1, *2	td(off)1	VDD = 10 V, VGS = 4 to 0 V		0.80		
Fall Time *1, *2	tf1	IS = 8.8 A		0.37		μs
Gate Resistance *1	Rg(CG)	f = 1 MHz	1	5	9	Ω

(MOSFET: DG FET)

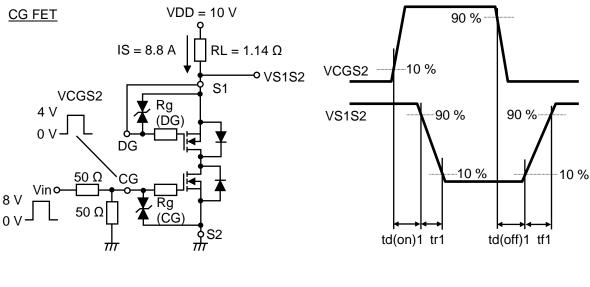
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Turn-on Delay Time *1, *2	td(on)2	VDD = 10 V, VGS = 0 to 4 V		2.0		
Rise Time *1, *2	tr2	IS = 8.8 A		2.9		μs
Turn-off Delay Time *1, *2	td(off)2	VDD = 10 V, VGS = 4 to 0 V		14		110
Fall Time *1, *2	tf2	IS = 8.8 A		6.6		μs
Gate Resistance *1	Rg(DG)	f = 1 MHz	400	700	1000	Ω

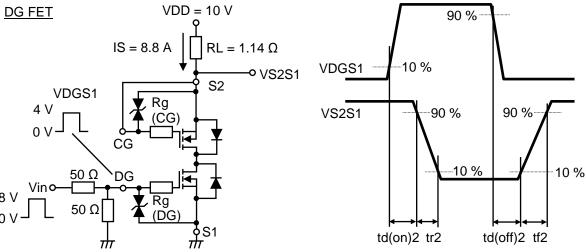
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

<sup>\*1</sup> Guaranteed by design, not subject to production testing.

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.

■ Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



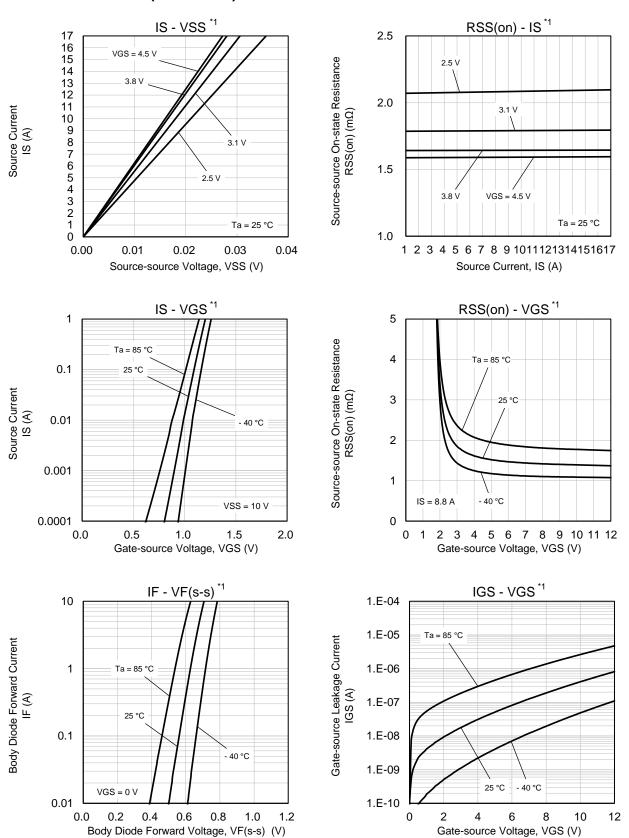


#### 8. ELECTROSTATIC DISCHARGE CHARACTERISTIC Ta = 25 °C ± 3 °C

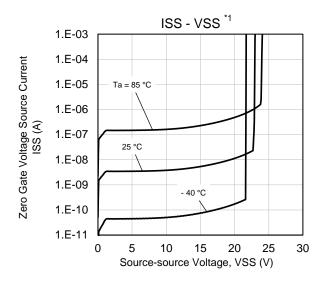
Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human Body Model	HBM	$C = 100 \text{ pF}, R = 1.5 \text{ k}\Omega$	H1C	$> 1k \text{ to } \leq 2k$	V

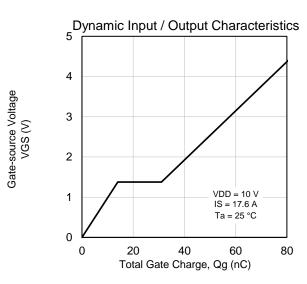


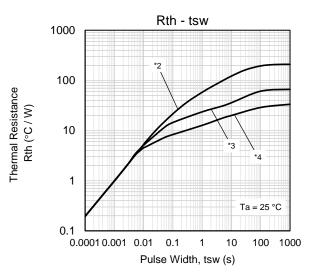
## 9. TECHNICAL DATA (Reference)

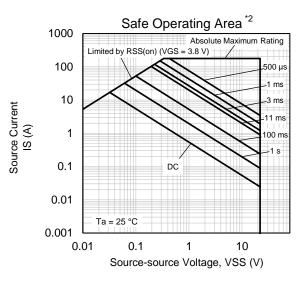


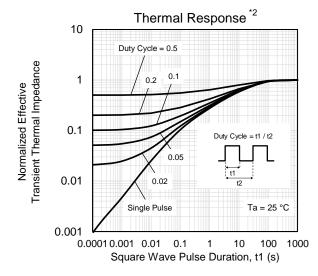
# **TECHNICAL DATA (Reference)**











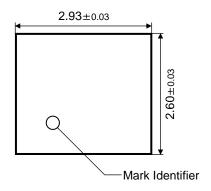
#### Note

- \*1 Pulse measurement.
- \*2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board partially covered with copper pad (41 mm² area, 36 µm thickness).
- \*3 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board fully covered with copper pad (612 mm² area, 36 µm thickness).
- \*4 Mounted on ceramic board (70 mm x 70 mm x t1.0 mm).



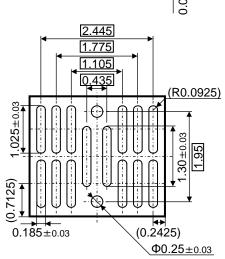
#### 10. OUTLINE

(Top View) Unit: mm

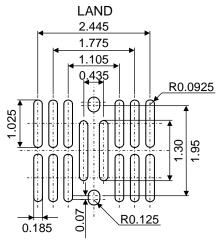


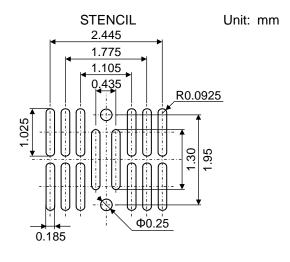
(Front View)

(Bottom View)



## 11. LAND & STENCIL PATTERN (Reference)





Important notice:

Solder Mask Defined (SMD) pattern is strongly recommended for pad design.

Please check the information in the Nuvoton WL-CSP Application Notes about mounting process.



# 12. REVISION HISTORY

Date	Revision	Description
2025.3.5	1.00	1. Initially issued.



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